

isc N-Channel MOSFET Transistor

SPP20N60C3, ISPP20N60C3

• FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 0.19\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

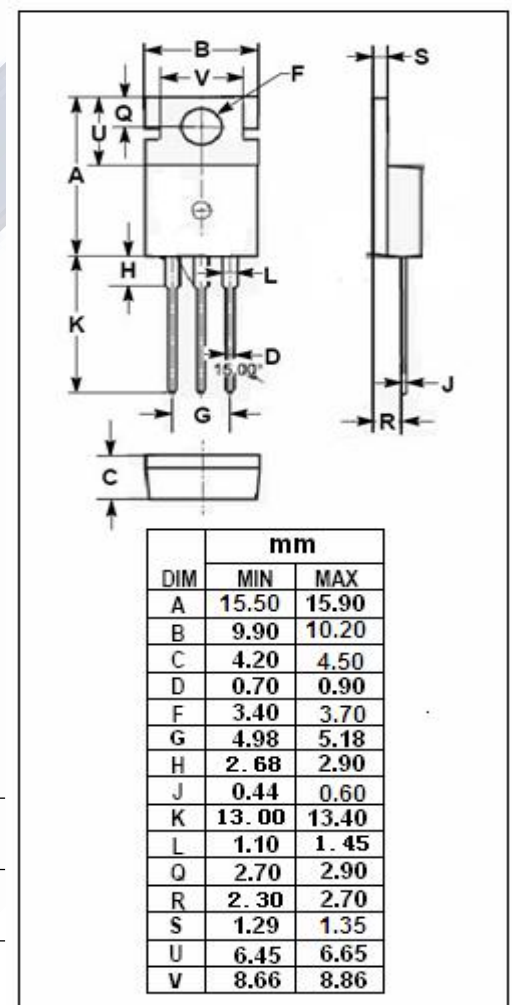
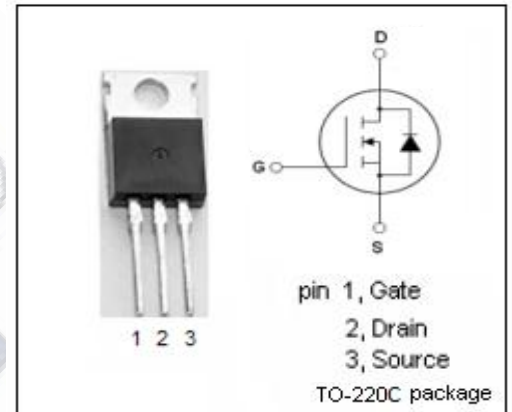
- Ultra low gate charge
- High peak current capability
- Improved transconductance

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	20.7	A
I_{DM}	Drain Current-Single Pulsed	62.1	A
P_D	Total Dissipation @ $T_c=25^\circ\text{C}$	208	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.6	$^\circ\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$; $I_D=0.25mA$	600			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=1mA$	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V$; $I_D=13.1A$			0.19	Ω
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=30V$; $V_{DS}=0V$			0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=600V$; $V_{GS}=0V$			1	μA
V_{SD}	Diode forward voltage	$I_F=I_S$; $V_{GS}=0V$			1.2	V